



### FCPF1300N80ZYD Information



For Reference Only

Part Number FCPF1300N80ZYD

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 800V 4A TO220FPackageTO-220-3 Full Pack, Formed Leads

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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### FCPF1300N80ZYD Specifications

Manufacturer Part Number         FCPF1300N80ZYD           Manufacturer         Fairchild/ON Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3 Full Pack, Formed Leads           Series         SuperFET? II           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         800V           Current - Continuous Drain (Id) @ 25°C         4A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4.5V @ 400μA           Gate Charge (Qg) (Max) @ Vgs         21nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         880pF @ 100V           Vgs (Max)         ±2F @ 100V           Vgs (Max)         ±2F @ 100V           Vgs (Max)         24W (Tc)           Rds On (Max) @ Id, Vgs         1.3 Ohm @ 2A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220F-3 (Y-Forming)           Package / Case         TO-220-3 Full Pack, Formed Leads		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3 Full Pack, Formed LeadsSeriesSuperFET? IIFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 400μAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds880pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)24W (Tc)Rds On (Max) @ Id, Vgs1.3 Ohm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	Manufacturer Part Number	FCPF1300N80ZYD
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FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Boov  Current - Continuous Drain (Id) @ 25°C  A4 (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.3 Ohm @ 2A, 10V  Operating Temperature  Mounting Type  Supplier Device Package  TO-220F-3 (Y-Forming)  Package / Case  N-Channel  MOSFET (Metal Oxide)  MOSFET (Metal Oxide)  880V  4.5V @ 400µA  4.5V @ 400µA	Package	TO-220-3 Full Pack, Formed Leads
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 400μAGate Charge (Qg) (Max) @ Vgs21nC @ 10VInput Capacitance (Ciss) (Max) @ Vds880pF @ 100VVgs (Max)±20VFET Feature-Power Dissipation (Max)24W (Tc)Rds On (Max) @ Id, Vgs1.3 Ohm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	Series	SuperFET? II
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Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.3 Ohm @ 2A, 10V  Operating Temperature  Supplier Device Package  TO-220F-3 (Y-Forming)  Package / Case  TO-220-3 Full Pack, Formed Leads	Drain to Source Voltage (Vdss)	800V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  880pF @ 100V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  24W (Tc)  Rds On (Max) @ Id, Vgs  1.3 Ohm @ 2A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220F-3 (Y-Forming)  Package / Case  TO-220-3 Full Pack, Formed Leads	Current - Continuous Drain (Id) @ 25°C	4A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  880pF @ 100V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.3 Ohm @ 2A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220F-3 (Y-Forming)  Package / Case  TO-220-3 Full Pack, Formed Leads	Drive Voltage (Max Rds On, Min Rds On)	10V
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Vgs (Max)±20VFET Feature-Power Dissipation (Max)24W (Tc)Rds On (Max) @ Id, Vgs1.3 Ohm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	Gate Charge (Qg) (Max) @ Vgs	21nC @ 10V
FET Feature -  Power Dissipation (Max) 24W (Tc)  Rds On (Max) @ Id, Vgs 1.3 Ohm @ 2A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220F-3 (Y-Forming)  Package / Case TO-220-3 Full Pack, Formed Leads	Input Capacitance (Ciss) (Max) @ Vds	880pF @ 100V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  1.3 Ohm @ 2A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220F-3 (Y-Forming)  Package / Case  TO-220-3 Full Pack, Formed Leads	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs1.3 Ohm @ 2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220F-3 (Y-Forming)Package / CaseTO-220-3 Full Pack, Formed Leads	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220F-3 (Y-Forming)  Package / Case  TO-220-3 Full Pack, Formed Leads	Power Dissipation (Max)	24W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Rds On (Max) @ Id, Vgs	1.3 Ohm @ 2A, 10V
Supplier Device Package TO-220F-3 (Y-Forming) Package / Case TO-220-3 Full Pack, Formed Leads	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack, Formed Leads	Mounting Type	Through Hole
	Supplier Device Package	TO-220F-3 (Y-Forming)
Report errors?	Package / Case	TO-220-3 Full Pack, Formed Leads
		Report errors?

#### FCPF1300N80ZYD Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

# FCPF1300N80ZYD Payment Methods



















### FCPF1300N80ZYD Shipping Methods













If you have any question about FCPF1300N80ZYD, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com